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REPORT DOCUMENTATION PAGE		AFRL-SR-B	AFRL-SR-BL-TR-01-		
Public reporting burden for this collection of in gathering and maintaining the data needed, ar collection of information, including suggestion Davis Highway, Suite 1204. Arlington, VA 22	s for reducing this burden, to Washington Hea 202-4302, and to the Office of Management a	response, information idquarters ind Budge CCC	52	kisting data sources, other aspect of this prts, 1215 Jefferson , DC 20503.	
1. AGENCY USE ONLY (Leave bla	ank) 2. REPORT DATE		al 15 Jun 95 to 14 Jun 98		
4. TITLE AND SUBTITLE AASERT-95 Femtosecond Near-Field Spin Microscopy of Magnetic/Superconducting Heterostructures			5. FUNDI 3484/US 61103D	NG NUMBERS	
6. AUTHOR(S) Dr David Awschalom					
7. PERFORMING ORGANIZATION University of California, Santa Quantum Institute Santa Barbara, CA 93106-5100				RMING ORGANIZATION AT NUMBER	
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) Air Force Office of Scientific Research 801 N. Randolph Street Arlington, VA 22203-1977			10. SPONSORING/MONITORING AGENCY REPORT NUMBER F49620-95-1-0434		
11. SUPPLEMENTARY NOTES AIR FORCE OFFICE OF SCIENTIFIC RESEARCH (AFOSR) NOTICE OF TRANSMITTAL DAYS. THEY STATEMENT Unlimited Distribution Notice of Transmittal Days. They are an and the point HAS BEEN REVIEWED AND IS APPROVED FOR PUBLIC RELEASE LAW AFR 190-12. DISTRIBUTION IS UNLIMITED.					
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14. SUBJECT TERMS				15. NUMBER OF PAGES	
17. SECURITY CLASSIFICATION OF REPORT	18. SECURITY CLASSIFICATION OF THIS PAGE	19. SECURITY CLASSIF OF ABSTRACT	ICATION 2	20. LIMITATION OF ABSTRAC	
Unclassified	Unclassified	Unclassified		UL	

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Standard Form 298 (Rev. 2-89) (EG) Prescribed by ANSI Std. 239.18 Designed using Perform Pro, WHS/DIOR, Oct 94

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AFOSR-AASERT Final Technical Report Grant #F49620-95-1-0434

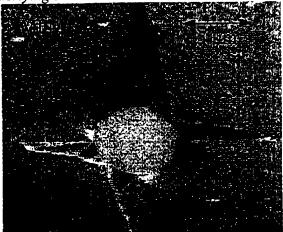
Femtosecond Near-field Spin Microscopy of Magnetic/Superconducting Heterostructures

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In contrast to embedding magnetic moments within a semiconductor heterostructure, it is important to demonstrate an ability to guide spin-dependent transport using field gradients from magnetic films grown upon a semiconductor heterostructure. The spin-dependent properties of these magnetically-patterned nanostructures is presently being resolved using both near-field scanning optical microscopy (NSOM) and magnetotransport studies. Under the AASERT program, our student developed magnetically active II-VI diluted magnetic semiconductor (DMS) surface quantum well "substrates" upon which to epitaxially grow and pattern ferromagnetic Fe films in order to produce spin-dependent potentials. This material phase produced a variety of fluxfocusing magnetic patterns including planar wedges and variable-spaced single domain particle arrays with nominally 0.1-0.5 micron feature sizes. These patterns are designed to create a field-driven spin-dependent energy landscape for optically-pumped or doped carriers and provide a basis for spatial measurements of electronic spin transport. Both insulating and conducting substrates have been prepared for the optical and transport measurements.

We have grown hybrid ferromagnetic-DMS quantum well structures by depositing typically 50 nm thick epitaxial films of Fe on top of a single ~ 12 nm quantum well containing 3 monolayers of Mn ions. Figure 1 shows an example of a recent result in collaboration with Dr. Gary Prinz of the Naval Research Laboratory. This wet-etched single-crystal Fe film was processed using a newly developed chemical technique, without any electronic degradation of the underlying semiconductor heterostructure.

Fig. 1. Magnetic force microscopy image of a 5 micron hole etched through a 50 nm-thick crystalline Fe film grown upon a 12 nm ZnSe/ZnCdSe quantum well containing 12-1/4 monolayer MnSe planes (a digital magnetic heterostructure). At B=0, star-shaped domain walls form to minimize the freeenergy of the in-plane field, creating large field gradients at the edges of the hole. For B>3 G, the domain walls sweep away leaving very large gradients around



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